

MOSFETs Silicon N-Channel MOS (DTMOS V)

# TK380P65Y

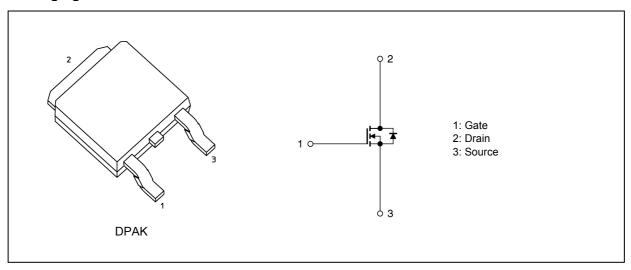
#### 1. Applications

· Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.29 \Omega$  (typ.) by using Super Junction Structure: DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th} = 3$  to 4 V ( $V_{DS} = 10$  V,  $I_D = 0.36$  mA)

#### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	650	V
Gate-source voltage			V <sub>GSS</sub>	±30	]
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>D</sub>	9.7	Α
Drain current (DC)	(T <sub>c</sub> = 100 °C)	(Note 1)	I <sub>D</sub>	6.1	Α
Drain current (pulsed)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>DP</sub>	38.8	Α
Power dissipation	(T <sub>c</sub> = 25 °C)		P <sub>D</sub>	80	W
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	96	mJ
Single-pulse avalanche current			I <sub>AS</sub>	2.5	Α
Reverse drain current (DC)		(Note 1)	I <sub>DR</sub>	9.7	1
Reverse drain current (pulsed)		(Note 1)	I <sub>DRP</sub>	38.8	Α
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	1.56	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 27.2 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AS}$  = 2.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	650	_	_	V
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.36 mA	3	_	4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.9 A	_	0.29	0.38	Ω

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}$	_	590	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	2.5	_	
Output capacitance	C <sub>oss</sub>		_	23	_	
Effective output capacitance	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V	_	41	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz	_	32	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	23	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	60	_	
Switching time (fall time)	t <sub>f</sub>		_	8.2	_	
Switching time (turn-off time)	t <sub>off</sub>		_	150	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}$ , $I_D \le 4.9 A$	50		-	V/ns

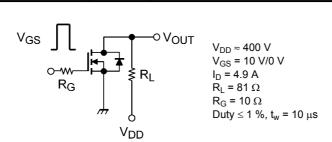


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 9.7 \text{ A}$		20		nC
Gate-source charge 1	Q <sub>gs1</sub>			3.2		
Gate-drain charge	$Q_{gd}$		_	10.5		

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 9.7 A, V <sub>GS</sub> = 0 V	1	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	V <sub>DD</sub> ≈ 400 V		240	_	ns
Reverse recovery charge	$Q_{rr}$	$I_{DR}$ = 4.6 A, $V_{GS}$ = 0 V -d $I_{DR}$ /dt = 100 A/ $\mu$ s	_	2	_	μС
Peak reverse recovery current	I <sub>rr</sub>	-αιρκ/αι – 100 Α/μο	_	17.5	_	Α
Diode dv/dt ruggedness	dv/dt	$V_{DS} \le 400 \text{ V}, I_{DR} \le 4.6 \text{ A}, V_{GS} = 0 \text{ V}$	15	_	_	V/ns



## 7. Marking

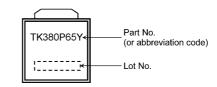


Fig. 7.1 Marking

### 8. Characteristics Curves (Note)

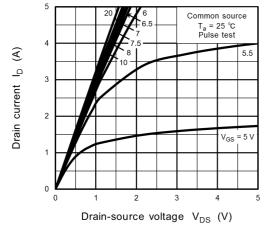
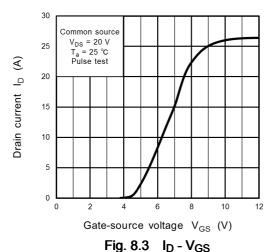


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



Drain-source voltage V<sub>DSS</sub> 650 600 550 500 L -100

Ambient temperature  $T_a$  (°C) Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

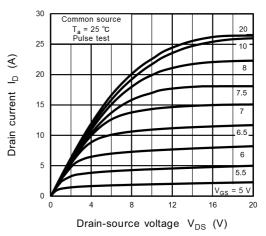


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

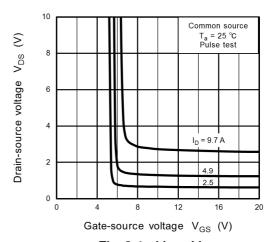


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

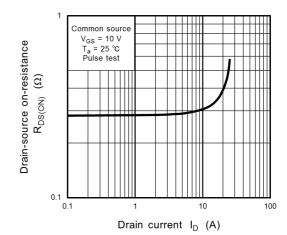


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

800

750

700

 $\leq$ 

Common source  $V_{GS} = 0 \text{ V}$   $I_D = 10 \text{ mA}$  Pulse test

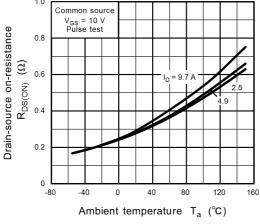


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

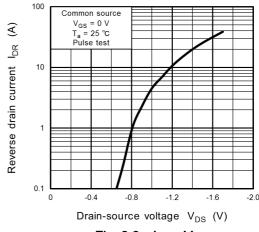


Fig. 8.8 IDR - VDS

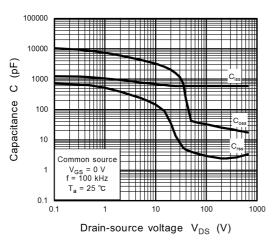


Fig. 8.9 C - V<sub>DS</sub>

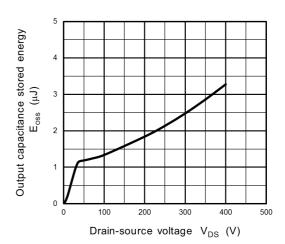


Fig. 8.10 Eoss - VDS

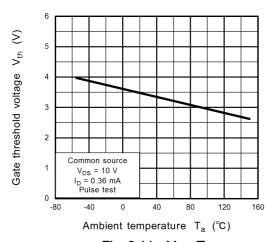


Fig. 8.11 V<sub>th</sub> - T<sub>a</sub>

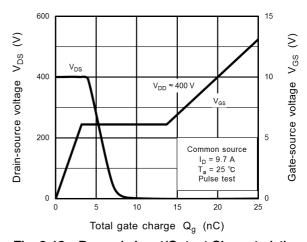


Fig. 8.12 Dynamic Input/Output Characteristics

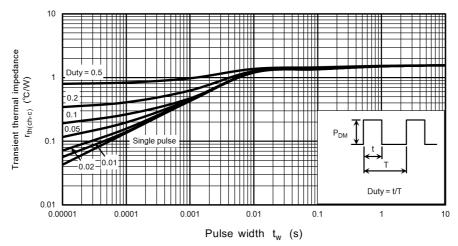


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

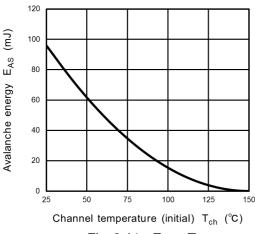


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

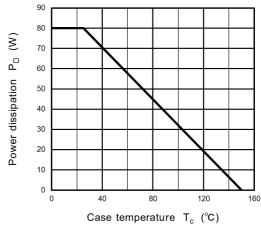
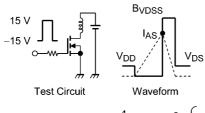


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)



 $R_G = 25 \Omega$ ,  $V_{DD} = 90 V$   $E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$ 

Fig. 8.16 Test Circuit/Waveform

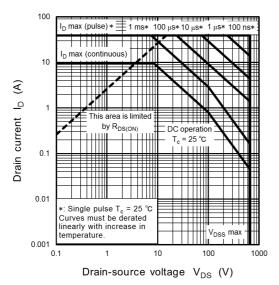


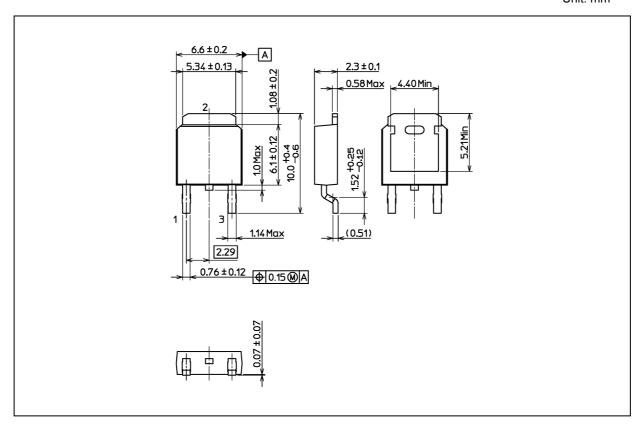
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)
TOSHIBA: 2-7K1S	
Nickname: DPAK	

Rev.1.0



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